

DAN222G

Common Cathode Silicon Dual Switching Diode

This Common Cathode Silicon Epitaxial Planar Dual Diode is designed for use in ultra high speed switching applications. This device is housed in the SOT-416/SC-75 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Fast t_{rr}
- Low C_D
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	80	Vdc
Peak Reverse Voltage	V_{RM}	80	Vdc
Forward Current	I_F	100	mAdc
Peak Forward Current	I_{FM}	300	mAdc
Peak Forward Surge Current (Note 1)	I_{FSM}	2.0	Adc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation	P_D	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}/\text{W}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

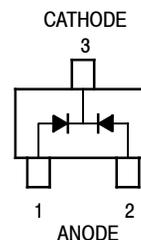
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. $t = 1 \mu\text{S}$



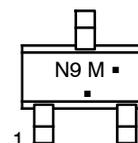
ON Semiconductor®

<http://onsemi.com>



SC-75/SOT-416
CASE 463
STYLE 3

MARKING DIAGRAM



N9 = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
DAN222G	SC-75/SOT-416 (Pb-Free)	3000/Tape & Reel
DAN222T1G	SC-75/SOT-416 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DAN222G

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Characteristic	Symbol	Condition	Min	Max	Unit
Reverse Voltage Leakage Current	I_R	$V_R = 70\text{ V}$	-	0.1	μA dc
Forward Voltage	V_F	$I_F = 100\text{ mA}$	-	1.2	Vdc
Reverse Breakdown Voltage	V_R	$I_R = 100\ \mu\text{A}$	80	-	Vdc
Diode Capacitance	C_D	$V_R = 6.0\text{ V}, f = 1.0\text{ MHz}$	-	3.5	pF
Reverse Recovery Time	t_{rr} (Note 2)	$I_F = 5.0\text{ mA}, V_R = 6.0\text{ V}, R_L = 100\ \Omega, I_{rr} = 0.1\ I_R$	-	4.0	ns

2. t_{rr} Test Circuit on following page.

TYPICAL ELECTRICAL CHARACTERISTICS

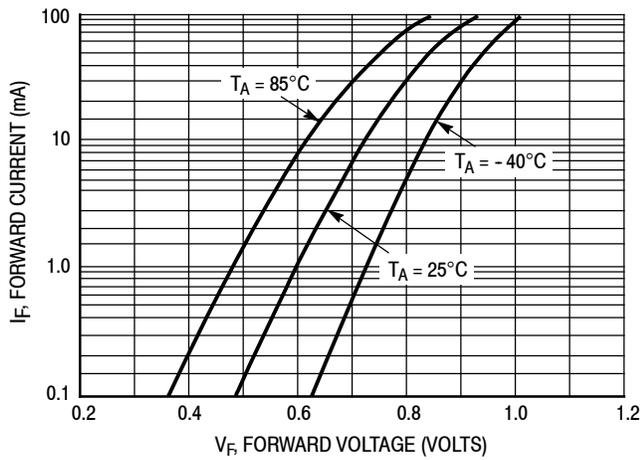


Figure 1. Forward Voltage

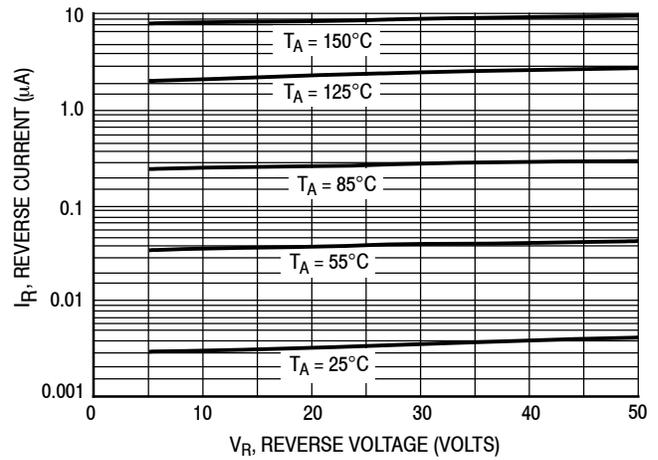


Figure 2. Reverse Current

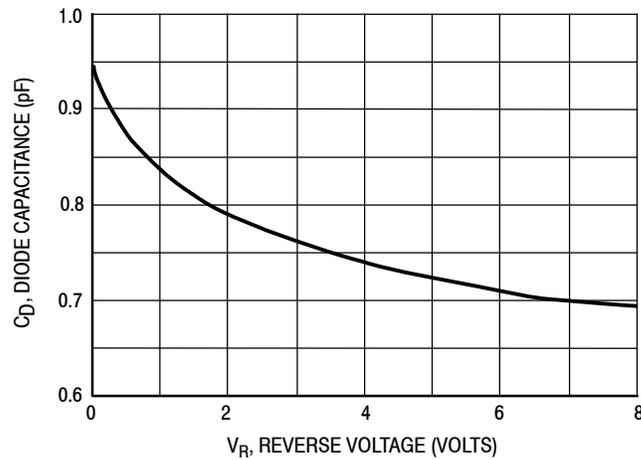
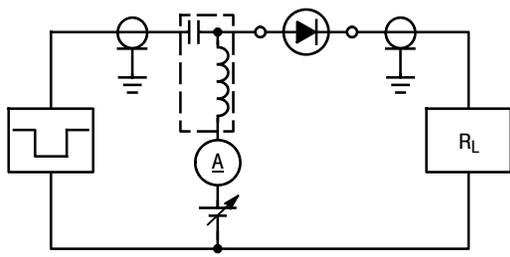
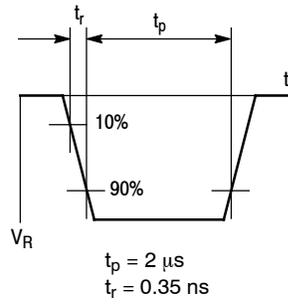


Figure 3. Diode Capacitance

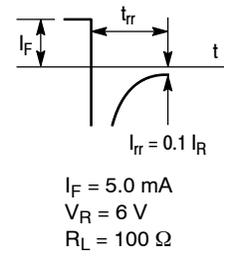
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RECOVERY TIME EQUIVALENT TEST CIRCUIT



INPUT PULSE



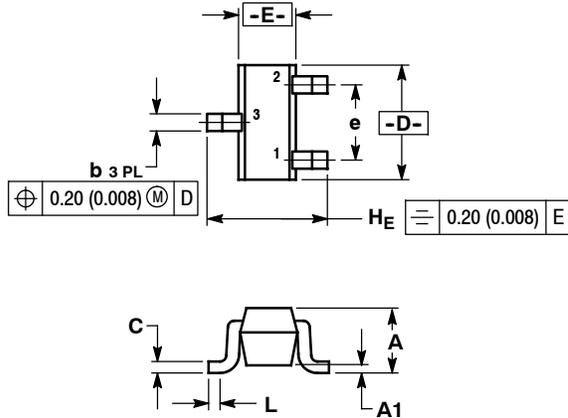
OUTPUT PULSE

Figure 4. Reverse Recovery Time Test Circuit for the DAN222

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PACKAGE DIMENSIONS

SC-75/SOT-416
CASE 463-01
ISSUE F

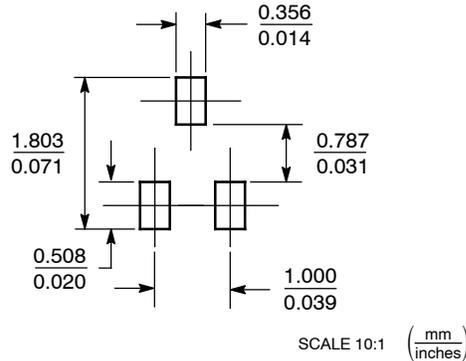


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
C	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.059	0.063	0.067
E	0.70	0.80	0.90	0.027	0.031	0.035
e	1.00 BSC			0.04 BSC		
L	0.10	0.15	0.20	0.004	0.006	0.008
H _E	1.50	1.60	1.70	0.061	0.063	0.065

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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